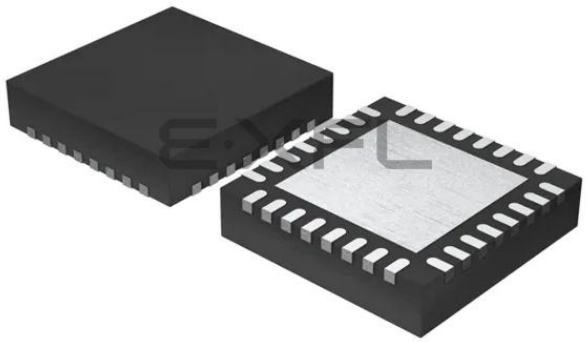

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	25MHz
Connectivity	I²C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	22
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 4x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-VQFN Exposed Pad
Supplier Device Package	32-QFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32hg310f64g-a-qfn32r

2.1.20 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 3 external pins and 6 internal signals.

2.1.21 Current Digital to Analog Converter (IDAC)

The current digital to analog converter can source or sink a configurable constant current, which can be output on, or sinked from pin or ADC. The current is configurable with several ranges of various step sizes.

2.1.22 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.23 General Purpose Input/Output (GPIO)

In the EFM32HG310, there are 22 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 13 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.2 Configuration Summary

The features of the EFM32HG310 is a subset of the feature set described in the EFM32HG Reference Manual. Table 2.1 (p. 6) describes device specific implementation of the features.

Table 2.1. Configuration Summary

Module	Configuration	Pin Connections
Cortex-M0+	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO,
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
CMU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
USB	Full configuration	USB_VREGI, USB_VREGO, USB_DM, USB_DMPU, USB_DP
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
USART0	Full configuration with IrDA and I2S	US0_TX, US0_RX. US0_CLK, US0_CS
USART1	Full configuration with I2S and IrDA	US1_TX, US1_RX, US1_CLK, US1_CS

3.4 Current Consumption

Table 3.3. Current Consumption

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{EM0}	EM0 current. No prescaling. Running prime number calculation code from Flash.	24 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		148	158	µA/MHz
		24 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		153	163	µA/MHz
		24 MHz USHFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		161	172	µA/MHz
		24 MHz USHFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		163	174	µA/MHz
		24 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		127	137	µA/MHz
		24 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		129	139	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		131	140	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		134	143	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		134	143	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		137	145	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		136	144	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		139	148	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		142	150	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		146	154	µA/MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		184	196	µA/MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		194	208	µA/MHz

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=85°C		1.6	3.50	µA
I_{EM3}	EM3 current	EM3 current (ULFRCO enabled, LFRCO/LFXO disabled), V_{DD}= 3.0 V, T_{AMB}=25°C		0.6	0.90	µA
		EM3 current (ULFRCO enabled, LFRCO/LFXO disabled), V_{DD}= 3.0 V, T_{AMB}=85°C		1.2	2.65	µA
I_{EM4}	EM4 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.02	0.035	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		0.18	0.480	µA

3.4.1 EM0 Current Consumption

Figure 3.1. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 24 MHz

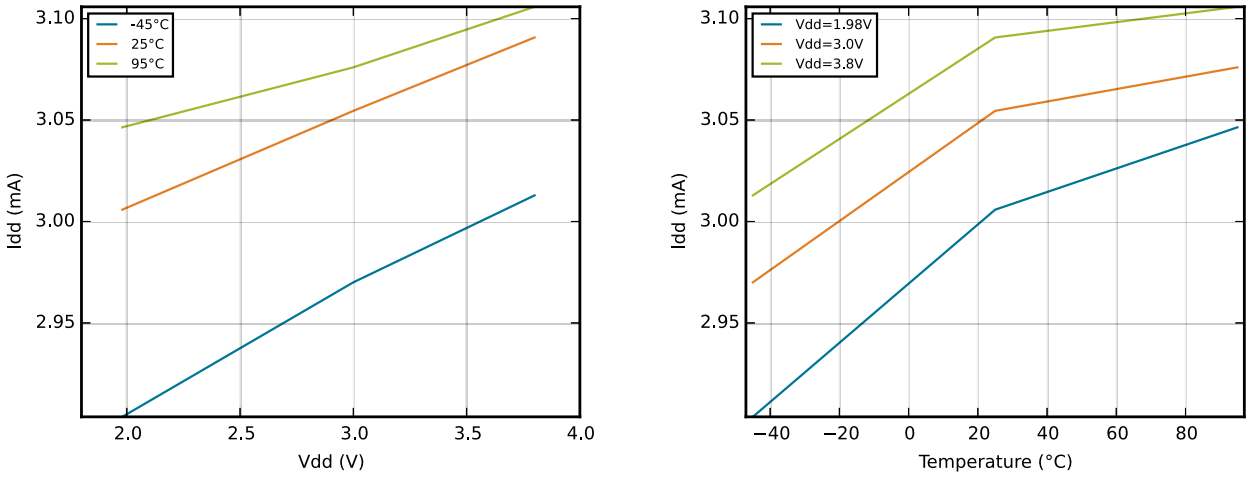


Figure 3.2. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 21 MHz

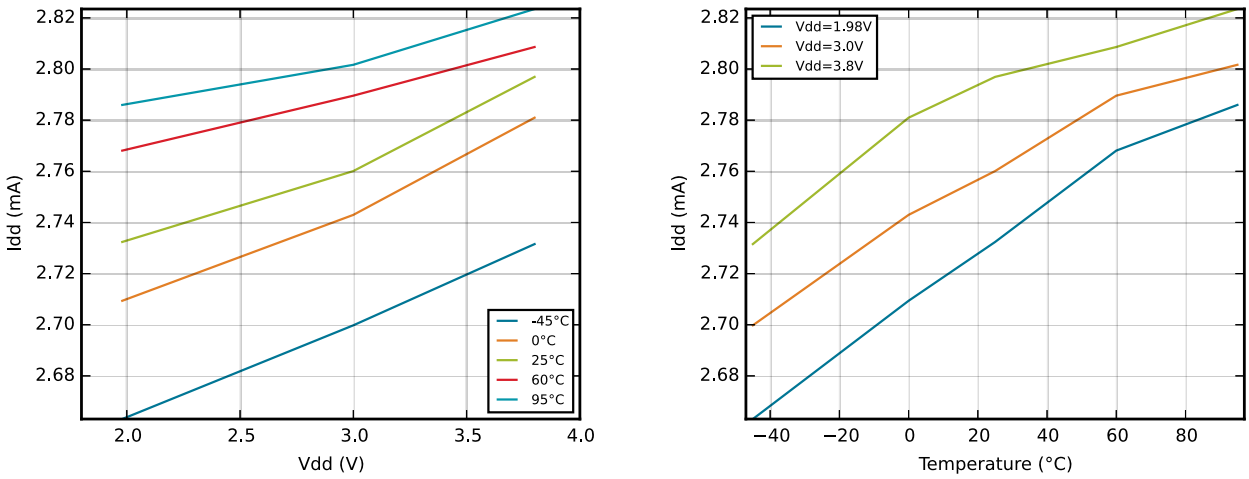


Figure 3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21 MHz

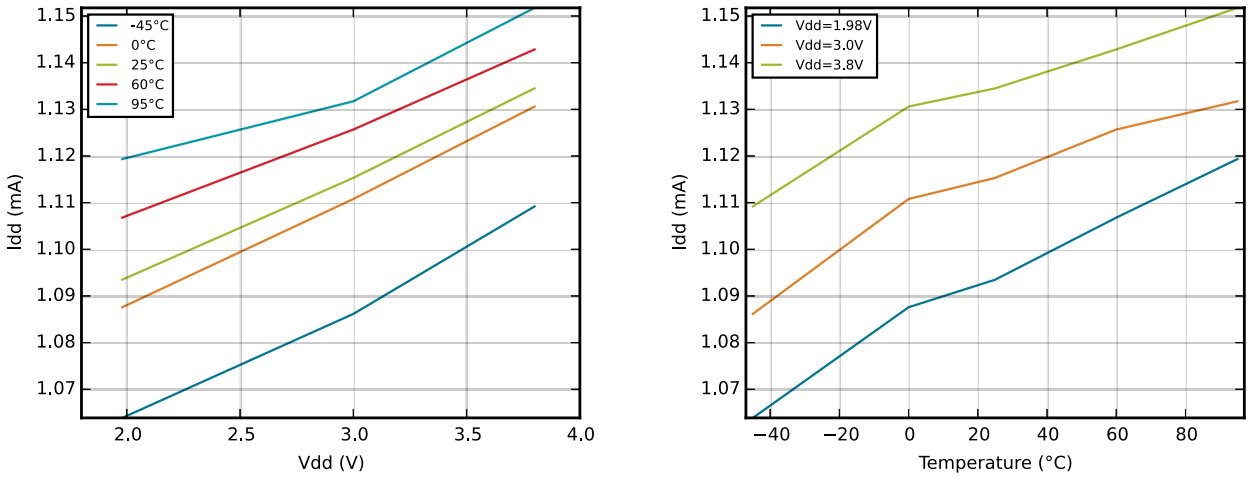
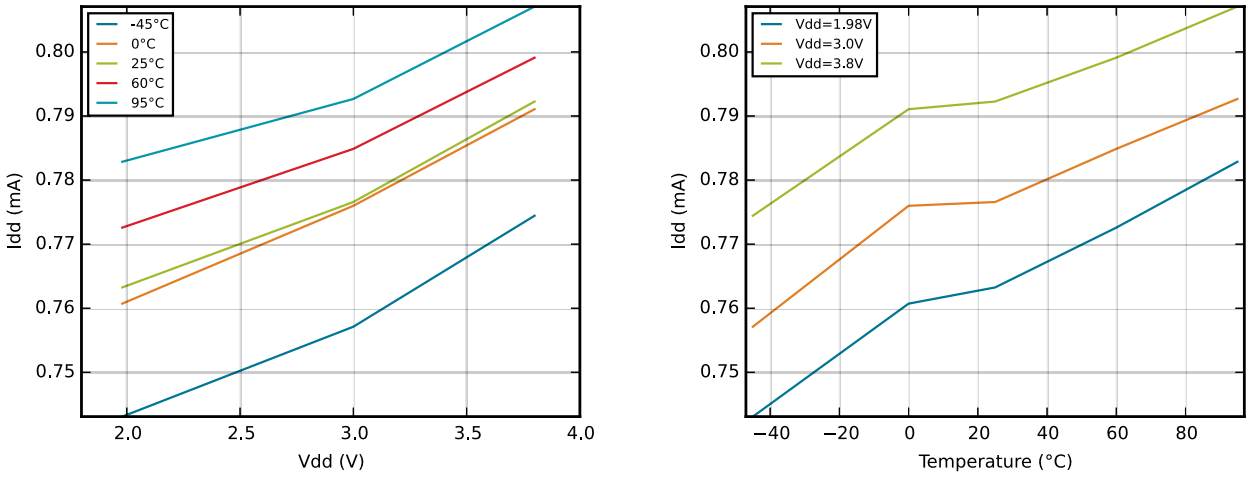
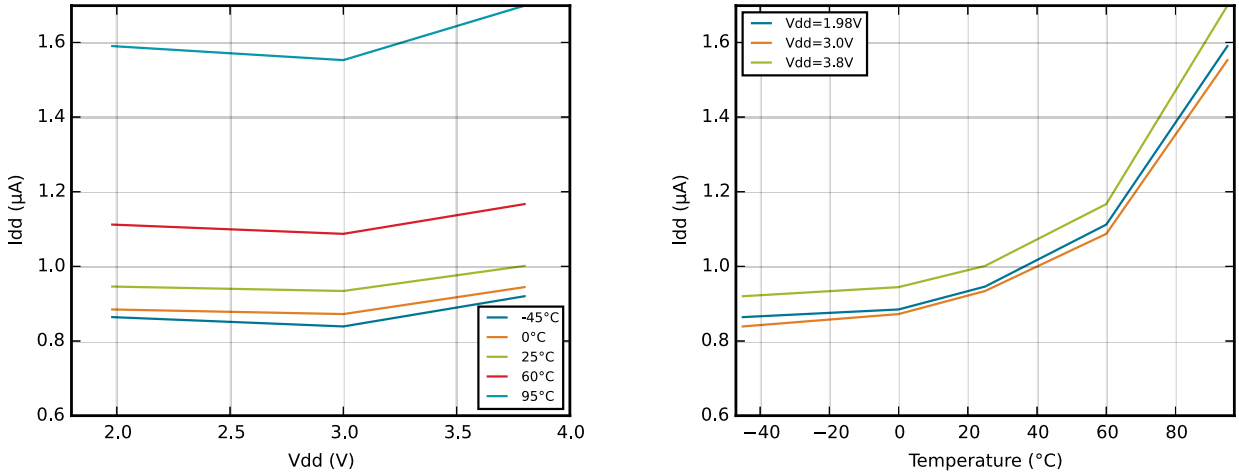


Figure 3.8. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14 MHz



3.4.3 EM2 Current Consumption

Figure 3.11. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.



3.4.4 EM3 Current Consumption

Figure 3.12. EM3 current consumption.

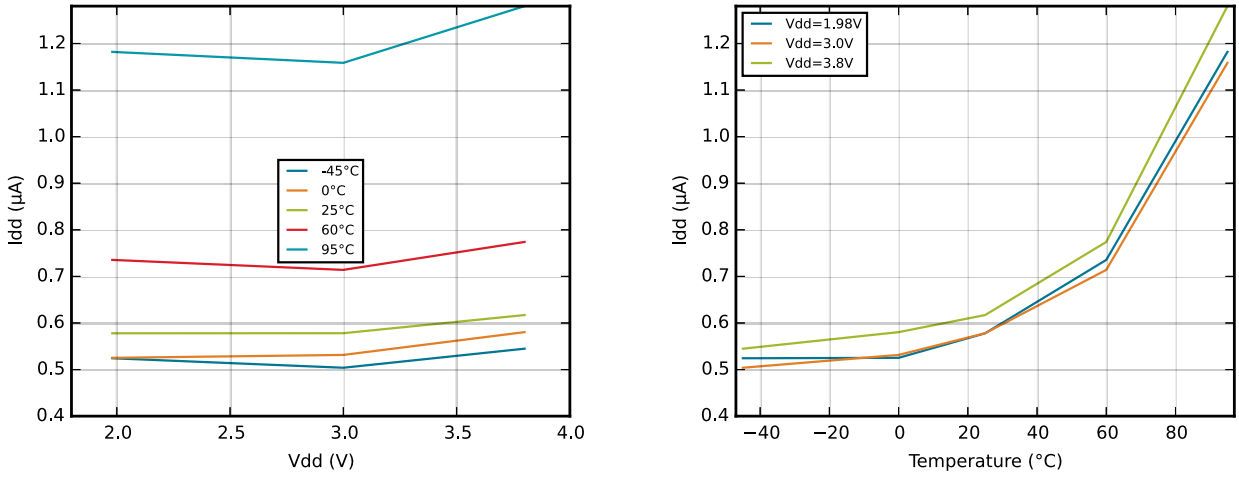


Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{BODextthr-}$	BOD threshold on falling external supply voltage	EM0	1.74		1.96	V
		EM2	1.71	1.86	1.98	V
$V_{BODextthr+}$	BOD threshold on rising external supply voltage			1.85		V
t_{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		µs
$C_{DECOUPLE}$	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		µF
C_{USB_VREGO}	USB voltage regulator out decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGO pin and GROUND		1		µF
C_{USB_VREGI}	USB voltage regulator in decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGI pin and GROUND		4.7		µF

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC_{FLASH}	Flash erase cycles before failure		20000			cycles
RET_{FLASH}	Flash data retention	T_{AMB}<150°C	10000			h
		T_{AMB}<85°C	10			years
		T_{AMB}<70°C	20			years
t_{W_PROG}	Word (32-bit) programming time		20			µs
t_{P_ERASE}	Page erase time		20	20.4	20.8	ms
t_{D_ERASE}	Device erase time		40	40.8	41.6	ms
I_{ERASE}	Erase current				7[1]	mA
I_{WRITE}	Write current				7[1]	mA
V_{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

[1] Measured at 25°C

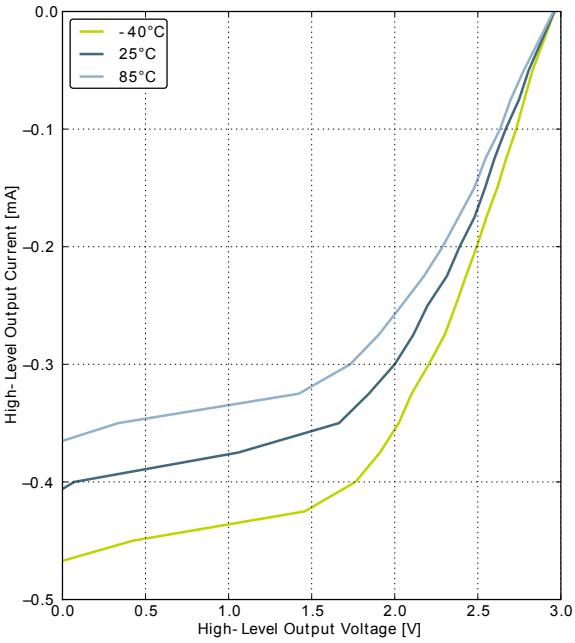
3.8 General Purpose Input Output

Table 3.7. GPIO

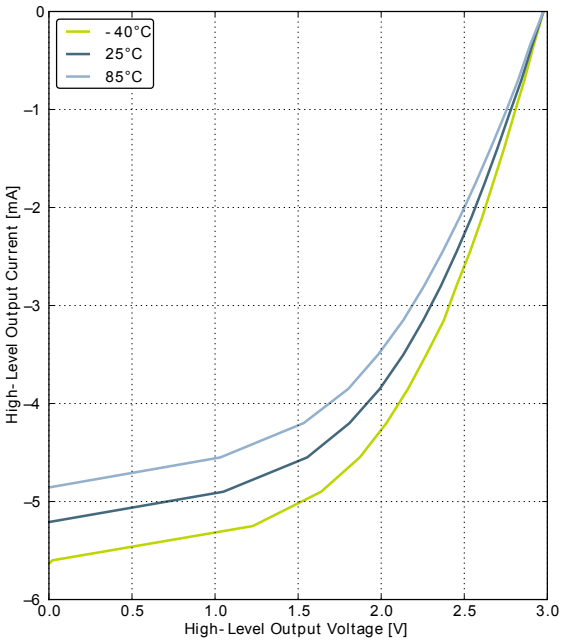
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				$0.30V_{DD}$	V
V_{IOIH}	Input high voltage		$0.70V_{DD}$			V

Symbol	Parameter	Condition	Min	Typ	Max	Unit
R_{PD}	I/O pin pull-down resistor			40		kOhm
R_{IOESD}	Internal ESD series resistor			200		Ohm
$t_{IOGLITCH}$	Pulse width of pulses to be removed by the glitch suppression filter		10		50	ns
t_{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capacitance C_L=12.5-25pF.	20+0.1C_L		250	ns
		GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance C_L=350-600pF	20+0.1C_L		250	ns
V_{IOHYST}	I/O pin hysteresis (V_{IOTHR+} - V_{IOTHR-})	V_{DD} = 1.98 - 3.8 V	0.1V_{DD}			V

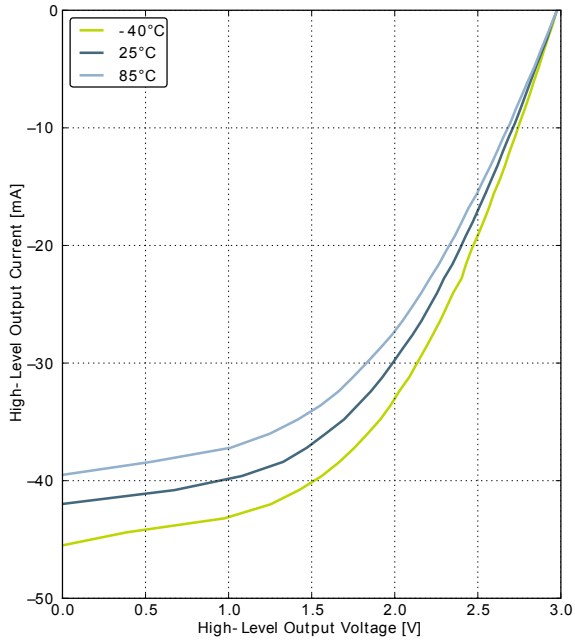
Figure 3.17. Typical High-Level Output Current, 3V Supply Voltage



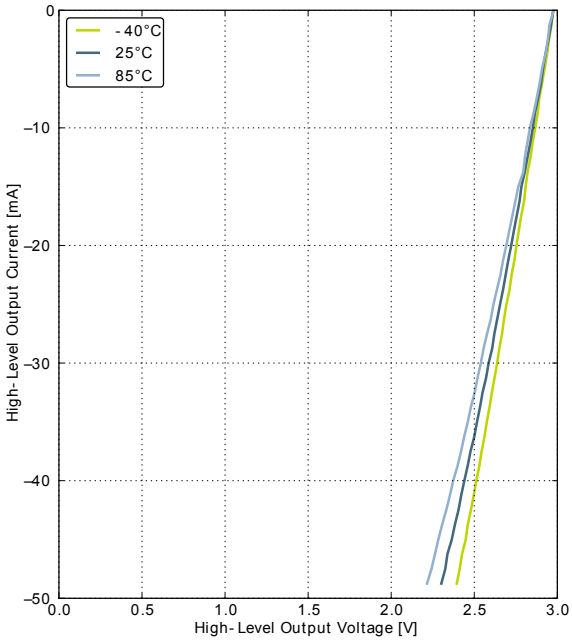
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

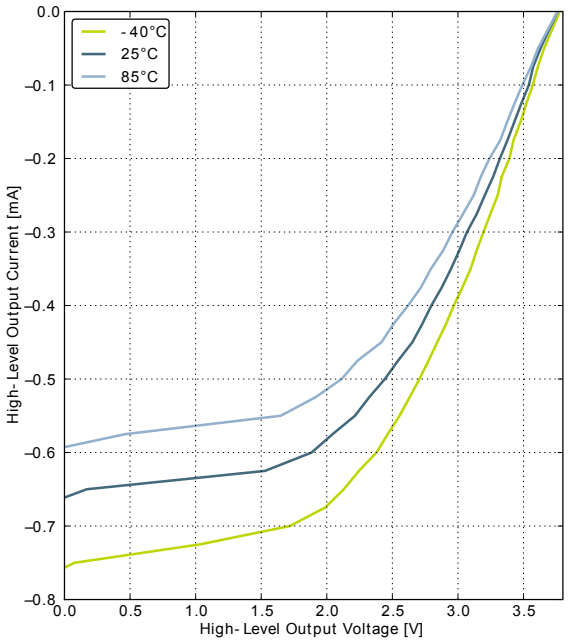


GPIO_Px_CTRL DRIVEMODE = STANDARD

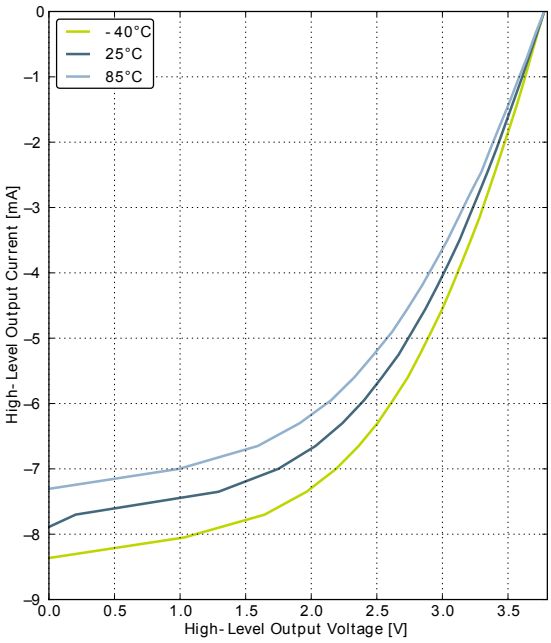


GPIO_Px_CTRL DRIVEMODE = HIGH

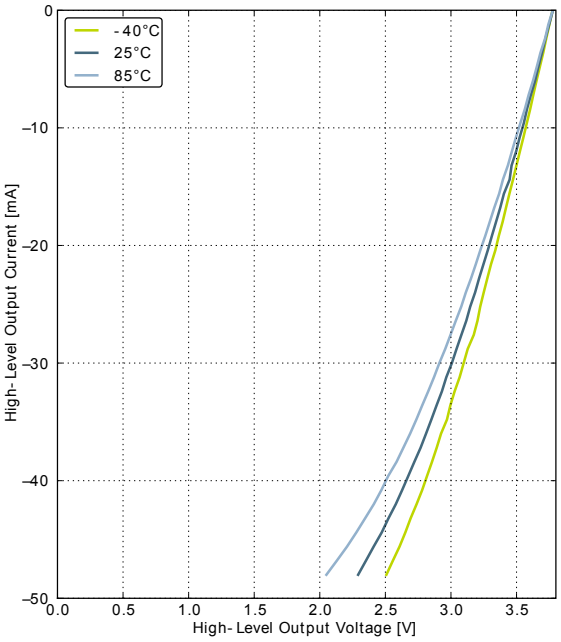
Figure 3.19. Typical High-Level Output Current, 3.8V Supply Voltage



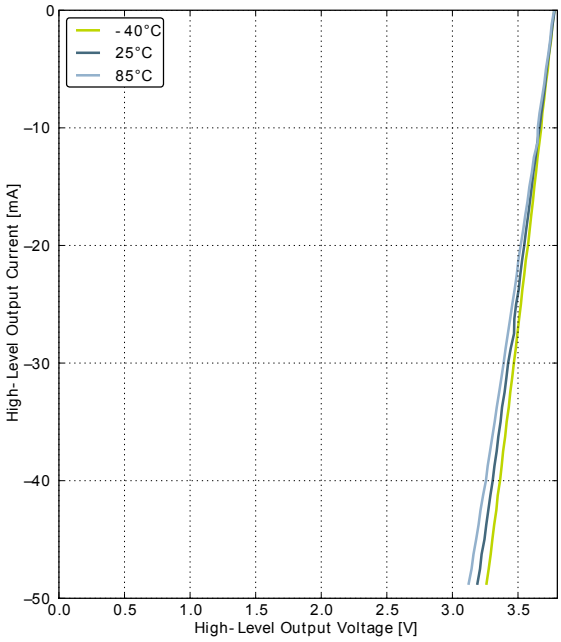
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		5		25	pF
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L=10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L=10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		1100		ms

For safe startup of a given crystal, the Configurator tool in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

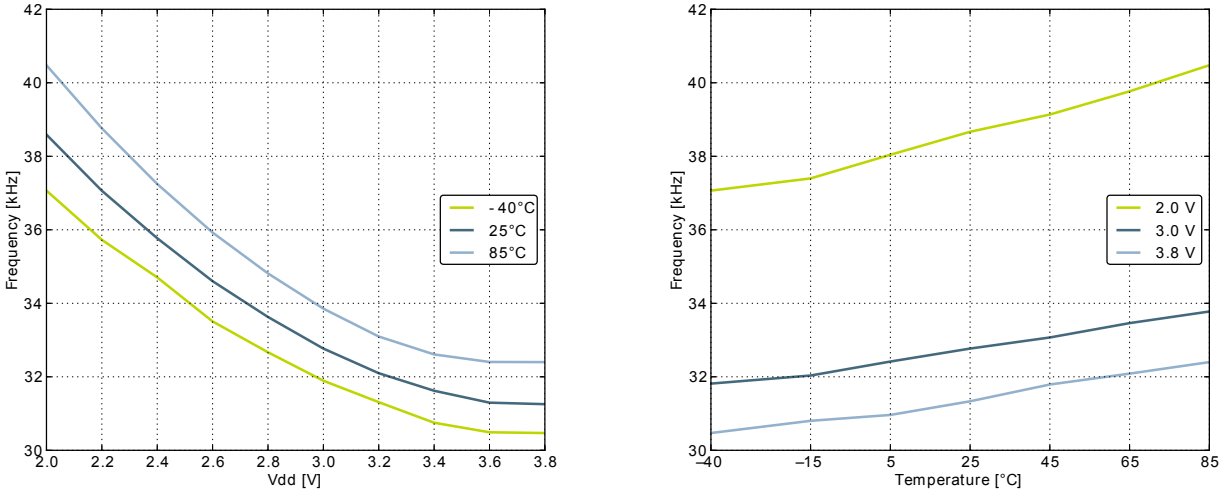
Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported frequency, any mode		4		25	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 25 MHz		30	100	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L=20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		µA
		25 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		µA
t_{HFXO}	Startup time	25 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		785		µs

3.9.3 LFRCO

Table 3.10. LFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFRCO}	Oscillation frequency , V_{DD}= 3.0 V, T_{AMB}=25°C		31.3	32.768	34.3	kHz
t_{LFRCO}	Startup time not including software calibration			150		µs
I_{LFRCO}	Current consumption			361	492	nA
$TUNESTEP_{LFRCO}$	Frequency step for LSB change in TUNING value			202		Hz

Figure 3.20. Calibrated LFRCO Frequency vs Temperature and Supply Voltage



3.9.4 HFRCO

Table 3.11. HFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFRCO}	Oscillation frequency, V_{DD}= 3.0 V, T_{AMB}=25°C	24 MHz frequency band	23.28	24.0	24.72	MHz
		21 MHz frequency band	20.37	21.0	21.63	MHz
		14 MHz frequency band	13.58	14.0	14.42	MHz
		11 MHz frequency band	10.67	11.0	11.33	MHz
		7 MHz frequency band	6.40	6.60	6.80	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
$t_{HFRCO\_settling}$	Settling time after start-up	f_{HFRCO} = 14 MHz		0.6		Cycles
I_{HFRCO}	Current consumption	f_{HFRCO} = 24 MHz		158	184	µA
		f_{HFRCO} = 21 MHz		143	175	µA
		f_{HFRCO} = 14 MHz		113	140	µA
		f_{HFRCO} = 11 MHz		101	125	µA
		f_{HFRCO} = 6.6 MHz		84	105	µA
		f_{HFRCO} = 1.2 MHz		27	40	µA
$TUNESTEP_{H-FRCO}$	Frequency step for LSB change in TUNING value	24 MHz frequency band		66.8[1]		kHz
		21 MHz frequency band		52.8[1]		kHz
		14 MHz frequency band		36.9[1]		kHz
		11 MHz frequency band		30.1[1]		kHz
		7 MHz frequency band		18.0[1]		kHz
		1 MHz frequency band		3.4		kHz

[1]The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 21 MHz across operating conditions.

Figure 3.21. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature

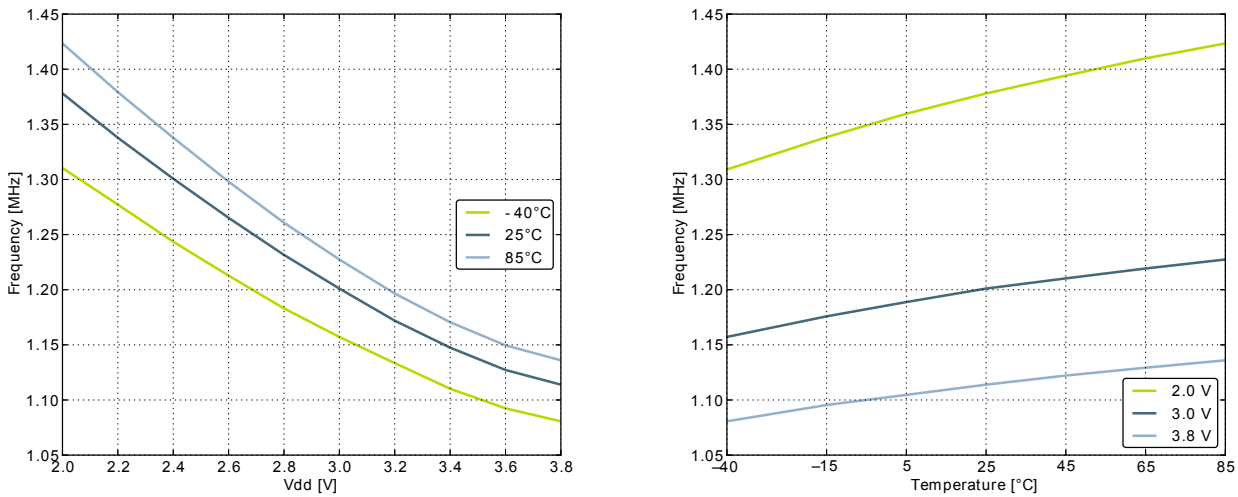
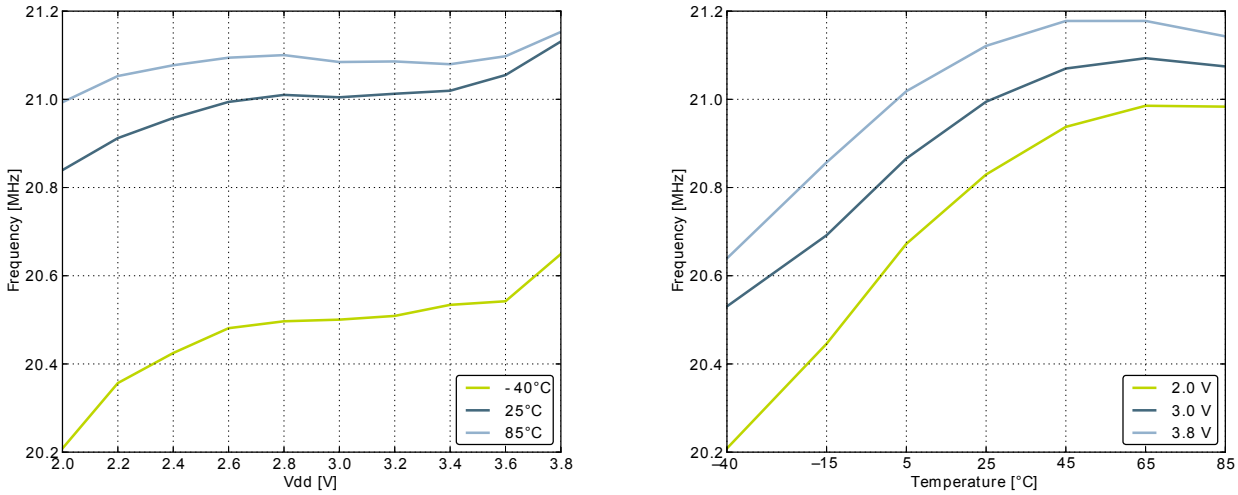


Figure 3.25. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature



3.9.5 AUXHFRCO

Table 3.12. AUXHFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$f_{AUXHFRCO}$	Oscillation frequency, V_{DD}= 3.0 V, T_{AMB}=25°C	21 MHz frequency band	20.37	21.0	21.63	MHz
		14 MHz frequency band	13.58	14.0	14.42	MHz
		11 MHz frequency band	10.67	11.0	11.33	MHz
		7 MHz frequency band	6.40	6.60	6.80	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
$t_{AUXHFRCO\_settling}$	Settling time after start-up	$f_{AUXHFRCO}$ = 14 MHz		0.6		Cycles
$TUNESTEP_{AUXHFRCO}$	Frequency step for LSB change in TUNING value	21 MHz frequency band		52.8		kHz
		14 MHz frequency band		36.9		kHz
		11 MHz frequency band		30.1		kHz
		7 MHz frequency band		18.0		kHz
		1 MHz frequency band		3.4		kHz

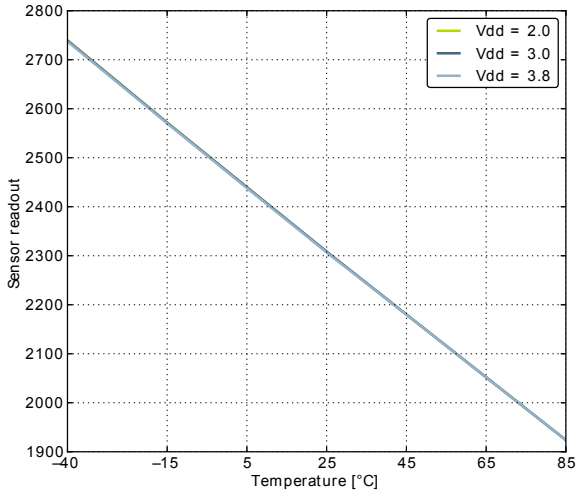
Symbol	Parameter	Condition	Min	Typ	Max	Unit
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		64		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		64		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		66		dB
		1 MSamples/s, 12 bit, differential, 2xV_{DD} reference		68		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		61		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		65		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		66		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	62	66		dB
		200 kSamples/s, 12 bit, differential, 2xV_{DD} reference		69		dB
$SFDR_{ADC}$	Spurious-Free Dynamic Range (SFDR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		64		dBc
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		76		dBc
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		73		dBc
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		66		dBc
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		77		dBc
		1 MSamples/s, 12 bit, differential, V_{DD} reference		76		dBc
		1 MSamples/s, 12 bit, differential, 2xV_{DD} reference		75		dBc
		1 MSamples/s, 12 bit, differential, 5V reference		69		dBc

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		76		dBc
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		79		dBc
		200 kSamples/s, 12 bit, differential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V_{DD} reference	68	79		dBc
		200 kSamples/s, 12 bit, differential, 2xV_{DD} reference		79		dBc
$V_{ADCOFFSET}$	Offset voltage	After calibration, single ended	-4	0.3	4	mV
		After calibration, differential		0.3		mV
$TGRAD_{ADCTH}$	Thermometer output gradient			-1.92		mV/°C
				-6.3		ADC Codes/ °C
DNL_{ADC}	Differential non-linearity (DNL)	V_{DD}= 3.0 V, external 2.5V reference	-1	±0.7	4	LSB
INL_{ADC}	Integral non-linearity (INL), End point method			±1.6	±3	LSB
MC_{ADC}	No missing codes		11.999[1]	12		bits
$VREF_{ADC}$	ADC Internal Voltage Reference	Internal 1.25V, V_{DD} = 3V, 25°C	1.248	1.254	1.262	V
		Internal 1.25V, Full temperature and supply range	1.188	1.254	1.302	V
		Internal 2.5V, V_{DD} = 3V, 25°C	2.492	2.506	2.520	V
		Internal 2.5V, Full temperature and supply range	2.402	2.506	2.600	V

[1]On the average every ADC will have one missing code, most likely to appear around 2048 ± n*512 where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.26 (p. 37) and Figure 3.27 (p. 37) , respectively.

Figure 3.33. ADC Temperature sensor readout



3.11 Current Digital Analog Converter (IDAC)

Table 3.16. IDAC Range 0 Source

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		13.0		µA
		Duty-cycled		10		nA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.85		µA
I_{STEP}	Step size			0.05		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = V_{DD} - 100mV		0.79		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0V, STEPSEL=0x10		0.3		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		11.7		nA/V

Table 3.17. IDAC Range 0 Sink

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		15.1		µA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.85		µA
I_{STEP}	Step size			0.05		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = 200 mV		0.30		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		0.2		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		12.5		nA/V

3.12 Analog Comparator (ACMP)

Table 3.25. ACMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ACMPIN}	Input voltage range		0		V_{DD}	V
V_{ACMPCM}	ACMP Common Mode voltage range		0		V_{DD}	V
I_{ACMP}	Active current	BIASPROG=0b0000, FULLBIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.4	µA
		BIASPROG=0b1111, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	15	µA
		BIASPROG=0b1111, FULLBIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		195	520	µA
$I_{ACMPREF}$	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0		µA
		Internal voltage reference		5		µA
$V_{ACMPOFFSET}$	Offset voltage	BIASPROG= 0b1010, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
$V_{ACMPHYST}$	ACMP hysteresis	Programmable		17		mV
R_{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		40		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		70		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		101		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		132		kOhm
$t_{ACMPSTART}$	Startup time				10	µs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 47) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

Total ACMP Active Current

$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF} \quad (3.1)$$

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
US1_TX	PC0		PD7	PD7	PF2	PC1		USART1 Asynchronous Transmit.Also used as receive input in half duplex communication. USART1 Synchronous mode Master Output / Slave Input (MOSI).
USB_DM	PC14							USB D- pin.
USB_DMPU	PA0							USB D- Pullup control.
USB_DP	PC15							USB D+ pin.
USB_VREGI	USB_VREGI							USB Input to internal 3.3 V regulator
USB_VREGO	USB_VREGO							USB Decoupling for internal 3.3 V USB regulator and regulator output

4.3 GPIO Pinout Overview

The specific GPIO pins available in *EFM32HG310* is shown in Table 4.3 (p. 56) . Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port is indicated by a number from 15 down to 0.

Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	-	-	-	-	-	-	-	-	-	-	-	-	-	PA2	PA1	PA0
Port B	-	PB14	PB13	-	PB11	-	-	PB8	PB7	-	-	-	-	-	-	-
Port C	PC15	PC14	-	-	-	-	-	-	-	-	-	-	-	-	PC1	PC0
Port D	-	-	-	-	-	-	-	-	PD7	PD6	PD5	-	-	-	-	-
Port E	-	-	PE13	PE12	PE11	PE10	-	-	-	-	-	-	-	-	-	-
Port F	-	-	-	-	-	-	-	-	-	-	-	-	-	PF2	PF1	PF0

7 Revision History

7.1 Revision 1.00

December 4th, 2015

Updated all specs with results of full characterization.

Updated part number to revision B.

Added the USB electrical specifications table.

7.2 Revision 0.91

May 6th, 2015

Updated current consumption table for energy modes.

Updated GPIO max leakage current.

Updated startup time for HFXO and LFXO.

Updated current consumption for HFRCO and LFRCO.

Updated ADC current consumption.

Updated IDAC characteristics tables.

Updated ACMP internal resistance.

Updated VCMP current consumption.

7.3 Revision 0.90

March 16th, 2015

Note

This datasheet revision applies to a product under development. It's characteristics and specifications are subject to change without notice.

Corrected EM2 current consumption condition in Electrical Characteristics section.

Updated GPIO electrical characteristics.

Updated Max ESR_{HFXO} value for Crystal Frequency of 25 MHz.

Updated LFRCO plots.

Updated HFRCO table and plots.

Updated ADC table and temp sensor plot.

Added DMA current in Digital Peripherals section.

Updated block diagram.

Updated Package dimensions table.

Corrected leadframe type to matte-Sn.

B Contact Information

Silicon Laboratories Inc.
400 West Cesar Chavez
Austin, TX 78701

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